



IFW

Docket No.: SON-3162

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Toshihiko Shirasagi, et al

Application No.: 10/579,211

Confirmation No.: 6592

Filed: May 12, 2006

Art Unit: 1756

For: MANUFACTURING METHOD OF MASTER  
DISC FOR OPTICAL DISC, AND MASTER  
DISC FOR OPTICAL DISC

Examiner: Not Yet Assigned

**SECOND INFORMATION DISCLOSURE STATEMENT (IDS)**

MS AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the requirements of 37 CFR §§ 1.56 and MPEP 609, the Applicant, through its representatives and attorneys, hereby provides for the attention of the examiner copies of the three non-patent documents cited at page 3 of the specification. This submission is timely in that it is made prior to a first action on the merits of the application. The relevance of these documents is noted at pages 1 to 5 of the specification as filed. Please take these documents into account along with the information at pages 1 to 5 of the specification as filed and make such consideration of record.

Applicant believes no fee is due with this response. However, if a fee is due, please charge our Deposit Account No. 18-0013, under Order No. SON-3162 from which the undersigned is authorized to draw.

Dated: February 15, 2007

Respectfully submitted,

By \_\_\_\_\_  
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PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/579,211 – Conf.# 6592
				Filing Date	May 12, 2006
				First Named Inventor	Toshihiko Shirasagi
				Art Unit	1756
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	SON-3162

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
					T <sup>6</sup>

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
	CA	N. Koshida et al., "50-nm Metal Line Fabrication by Focused Ion Beam and Oxide Resists," Japanese Journal of Applied Physics, Vol. 30, No. 11B, November 1991, pp. 3246-3249			
	CB	S. M. Gorwadkar et al., "SiO <sub>2</sub> /c-Si Bilayer Electron-Beam Resist Process for Nano-Fabrication," Japanese Journal of Applied Physics, Vol. 35 (1996), Part 1, No. 12B, pp. 6673-6678, December 1996			
	CC	S. A. Kostyukevych, "Investigations and modeling of physical processes in inorganic resists for the use in UV and laser lithography," Institute of Physics of Semiconductors, National Academy of Sciences Prospect Nauki 45, Kiev, 252028, UKRAINE, part of the SPIE Conference on Inorganic Optical Materials, California, SPIE Vol. 3424, July 1998			

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<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature		Date Considered	
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